

# **isc Silicon NPN Darlington Power Transistor**

2SD1793

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 100V (Min.)
- · High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

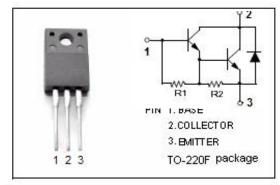
 Designed for audio frequency power amplifier and low speed high current switching industrial use.

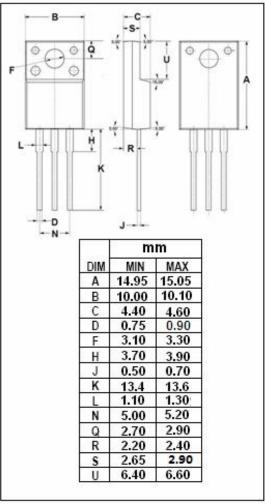
## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

ADSOLUTE MAXIMUM KATINGS(1a-25C)							
SYMBOL	PARAMETER	VALUE	UNIT				
Vceo	Collector-Emitter Voltage	100	V				
V <sub>CBO</sub>	Collector-Base Voltage	100	V				
V <sub>EBO</sub>	Emitter-Base Voltage	7	V				
Ic	Collector Current-Continunous	10	А				
I <sub>CM</sub>	Collector Current-Peak	15	А				
I <sub>B</sub>	Base Current-Continunous	0.5	Α				
Івм	Base Current-Peak	1.0	А				
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃		W				
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$				
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
Rth j-c	Thermal Resistance, Junction to Case		°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

10-23 C um	16-23 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT				
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 10mA			1.5	V				
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 10mA			2.0	V				
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			0.1	mA				
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 100V; I <sub>B</sub> = 0			0.1	mA				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			5	mA				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A, V <sub>CE</sub> = 3V	1500		30000					
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V		20		MHz				
Switching T	Switching Times; Resistive Load									
ton	Turn-On Time				2	μS				
t <sub>s</sub>	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = 5mA; I <sub>B2</sub> = 10mA; V <sub>BB2</sub> = 4V; R <sub>L</sub> = 6 Ω			12	μS				
t <sub>f</sub>	Fall Time				5	μ <b>s</b>				

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